

NPN SILICON RF POWER TRANSISTOR

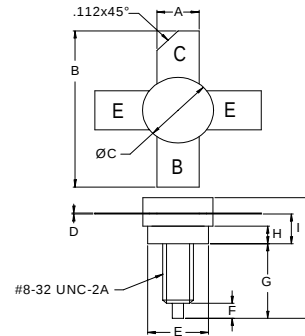
DESCRIPTION:

The **MRF238** is Designed for
13.6 V FM Large-Signal Amplifier
Applications to 175 MHz.

MAXIMUM RATINGS

I_C	5.0 A (CONT)
V_{CE}	18 V
V_{CB}	60 V
P_{DISS}	65 W @ $T_C = 25^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$

PACKAGE STYLE .380" 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 15\text{ mA}$	36			V
BV_{CEO}	$I_C = 100\text{ mA}$	18			V
BV_{EBO}	$I_E = 5.0\text{ mA}$	4.0			V
I_{CBO}	$V_{CB} = 30\text{ V}$			2.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 1.0\text{ A}$	5.0			---
C_{ob}	$V_{CB} = 15\text{ V}$ $f = 1.0\text{ MHz}$		105	130	pF
G_{PE} η	$V_{CC} = 13.6\text{ V}$ $P_{out} = 30\text{ W}$ $f = 160\text{ MHz}$	9.0 60	10		dB %